

2SB755

SILICON PNP TRIPLE DIFFUSED TYPE (PCT PROCESS)

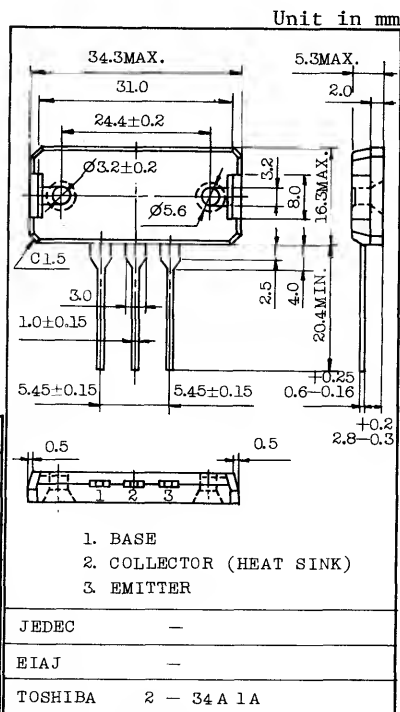
POWER AMPLIFIER APPLICATIONS.

FEATURES:

- High Breakdown Voltage : $V_{CEO} = -150V$ (Min.)
- High Transition Frequency : $f_T = 20MHz$ (Typ.)
- Complementary to 2SD845.
- Recommended for 80W High-Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-150	V
Collector-Emitter Voltage	V_{CEO}	-150	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-12	A
Emitter Current	I_E	12	A
Collector Power Dissipation ($T_c = 25^\circ C$)	P_C	120	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$



Weight : 10.8g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -150V, I_E = 0$	-	-	-50	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	-	-	-50	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -0.1A, I_B = 0$	-150	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10mA, I_C = 0$	-5	-	-	V
DC Current Gain	h_{FE} (Note)	$V_{CE} = -5V, I_C = -1A$	55	-	160	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -5V, I_B = -0.5A$	-	-	-2.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -5V, I_C = -5A$	-	-	-1.5	V
Transition Frequency	f_T	$V_{CE} = -10V, I_C = -1A$	-	20	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	-	450	-	pF

Note : h_{FE} Classification R : 55~110, 0 : 80~160

